

TC74HC573AP, TC74HC573AF, TC74HC573AFW**OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT**

The TC74HC573A is a high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. Its 8-bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

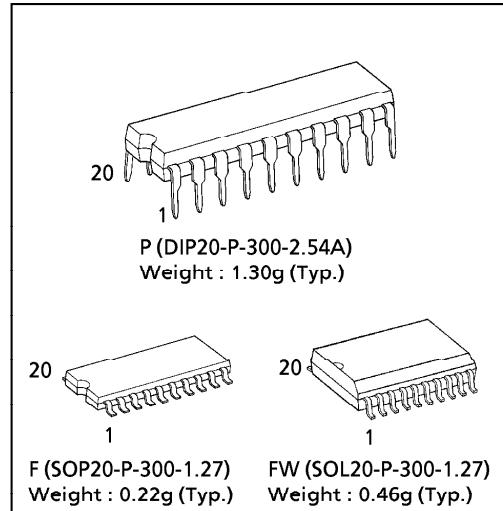
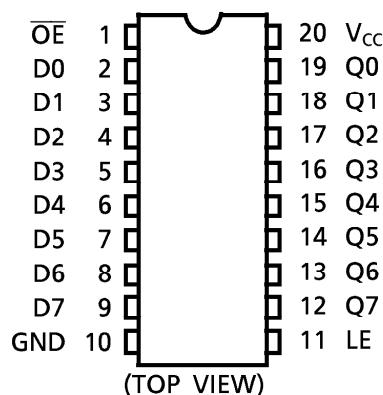
When the \overline{OE} input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

- High Speed..... $t_{pd} = 13\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability.....15 LSTTL Loads
- Symmetrical Output Impedance..... $|I_{OH}| = I_{OL} = 6\text{mA}(\text{Min.})$
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range..... V_{CC} (opr.) = 2V~6V
- Pin and Function Compatible with 74LS573

(Note) The JEDEC SOP (FW) is not available in Japan.

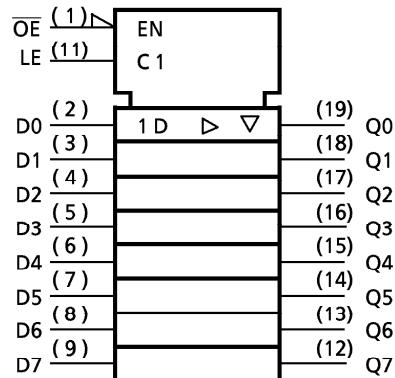
**PIN ASSIGNMENT****TRUTH TABLE**

INPUTS			OUTPUT
\overline{OE}	LE	D	Q
H	X	X	HZ
L	L	X	Q_n
L	H	L	L
L	H	H	H

X: Don't Care

HZ: High Impedance

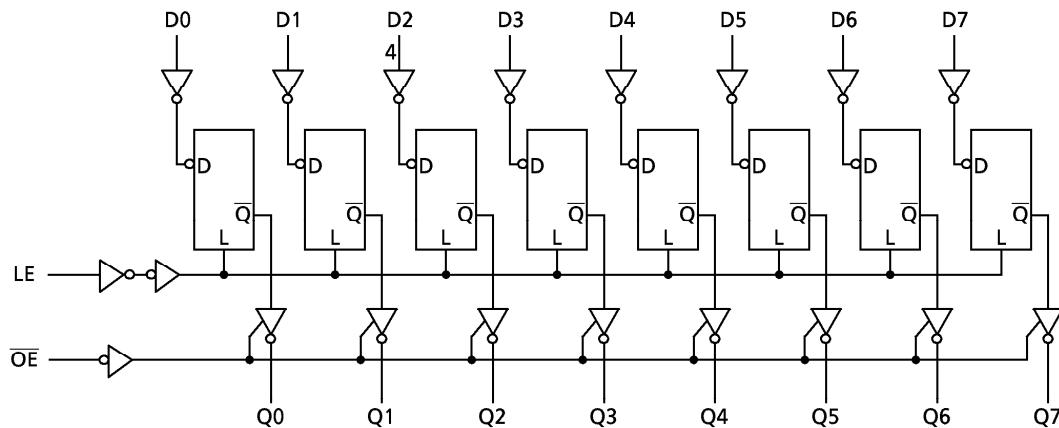
Q_n (\overline{Q}_n): Q (\overline{Q}) outputs are latched at the time when the LE input is taken to a low logic level.

IEC LOGIC SYMBOL

961001EBA2

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SYSTEM DIAGRAM



961001EBA2'

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 35	mA
DC V_{CC} / Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{STG}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	—	—	1.50 3.15 4.20	—	V
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	V
			$I_{OH} = -6\text{ mA}$ $I_{OH} = -7.8\text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
			$I_{OL} = 6\text{ mA}$ $I_{OL} = 7.8\text{ mA}$	4.5 6.0	0.17 0.18	0.26 0.26	— —	0.33 0.33	
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	6.0	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0	

TIMING REQUIREMENTS (Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	Ta = 25°C		Ta = -40~85°C	UNIT
				TYP.	LIMIT	LIMIT	
Minimum Pulse Width (LE)	$t_{W(H)}$		2.0	—	75	95	ns
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Set-up Time (Data)	t_s		2.0	—	50	65	
			4.5	—	10	13	
			6.0	—	9	11	
Minimum Hold Time (Data)	t_h		2.0	—	5	5	
			4.5	—	5	5	
			6.0	—	5	5	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	CL (pF)	V_{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}		50	2.0	—	20	60	—	75	ns
				4.5	—	6	12	—	15	
				6.0	—	5	10	—	13	
Propagation Delay Time (LE-Q, \bar{Q})	t_{PLH}		50	2.0	—	50	115	—	145	ns
				4.5	—	15	23	—	29	
				6.0	—	13	20	—	25	
	t_{PHL}		150	2.0	—	60	155	—	195	
Propagation Delay Time (D-Q, \bar{Q})	t_{PLH}		50	2.0	—	42	110	—	140	ns
				4.5	—	14	22	—	28	
				6.0	—	12	19	—	24	
	t_{PHL}		150	2.0	—	57	150	—	190	
Output Enable time	t_{PZL}	$R_L = 1\text{k}\Omega$	50	2.0	—	55	140	—	175	
				4.5	—	17	28	—	35	
				6.0	—	14	24	—	30	
	t_{PZH}		150	2.0	—	66	180	—	225	
Output Disable time	t_{PLZ} t_{PHZ}	$R_L = 1\text{k}\Omega$	50	2.0	—	40	125	—	155	
				4.5	—	17	25	—	31	
				6.0	—	15	21	—	26	
Input Capacitance	C_{IN}			—	5	10	—	10		pF
Output Capacitance	C_{OUT}			—	10	—	—	—		
Power Dissipation Capacitance	C_{PD} (1)			—	51	—	—	—		

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

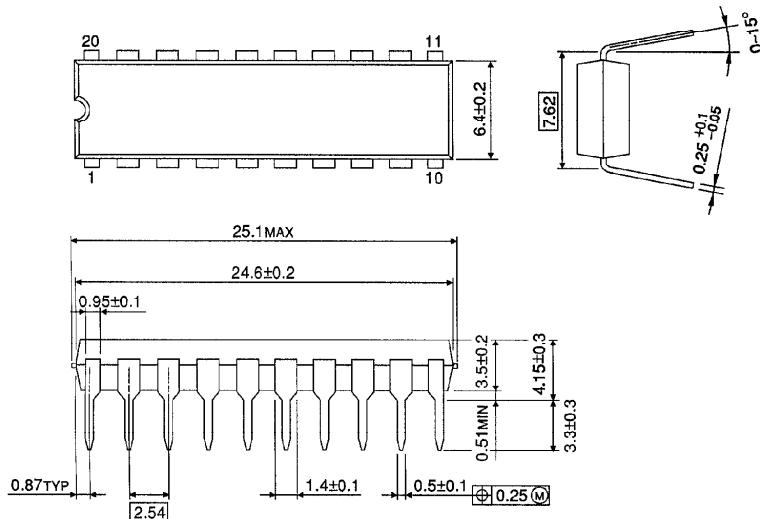
$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per Latch)}$$

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation:

$$C_{PD(\text{total})} = 33 + 18 \cdot n$$

DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

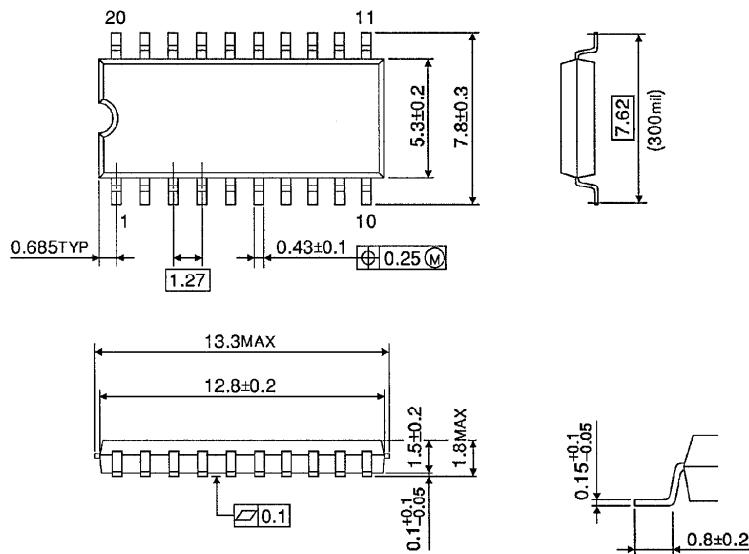
Unit in mm



Weight : 1.30g (Typ.)

SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

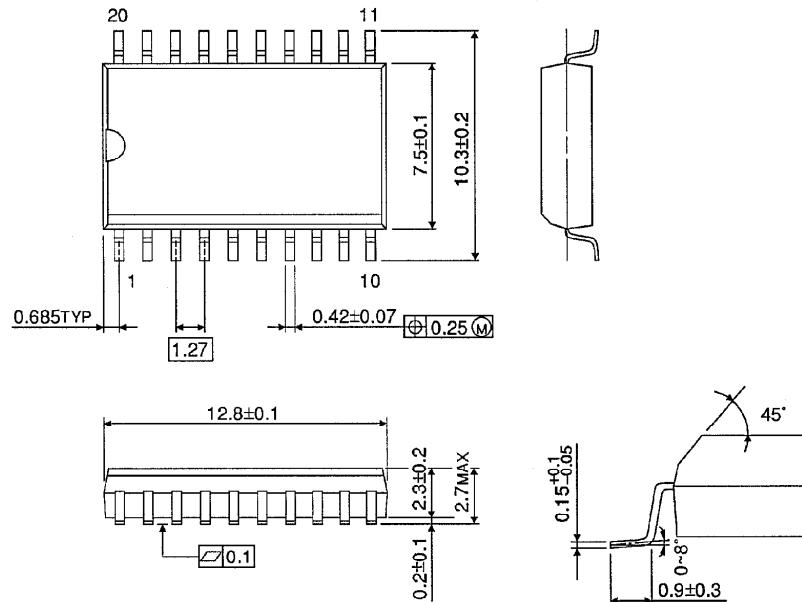


Weight : 0.22g (Typ.)

SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)